



Photodiodes

Device No.	Description	$\frac{BV}{I_R = 5.0 \mu A, H \leq 0.1 \mu W/cm^2}$		V_R V	$\frac{I_R}{V_R = -10V, H \leq 0.1 \mu W/cm^2}$		$\frac{I_{LT}}{V_R = -10V, H = 20 mW/cm^2}$	
		Min	Typ		Typ	Max	Min	Typ
FPT102	Photodiode Hermetic Package	50	20	50	0.1	25	12	20
FPT720	Photodiode T1 Clear Epoxy	120	160	50	0.3	35	15	25

Device No.	Description	R(Tungsten) Responsivity $\mu A/mW/cm^2$ TC = 2854°K		R @ 0.9 μ Responsivity $\mu A/mW/cm^2$ No bias, GaAs Typ	Package No.
		Min	Typ		
FPT102	Photodiode Hermetic Package	0.6	1.0	3.0	27
FPT720	Photodiode T1 Clear Epoxy	0.6	1.0	3.9	11

Photoemitters

Device No.	Description	I_F mA Max	V_F $I_F = 100$ mA V Typ	Wave Length (@ Peak Emission nm Typ	Axial Intensity $I_F = 100$ mA mW/sr Typ	Package No.
FPE100	Metal Header Package Wide Beam	100	1.35	890	0.3	Opto-32
FPE104	Lead Frame Package Narrow Beam	100	1.35	890	10	Opto-8
FPE500	TO-18, Dome Lens	250	1.35	890	10	Opto-29
FPE510	TO-18, Flat Lens	250	1.35	890	1.0	Opto-30
FPE520	TO-18, Dome Lens	250	1.35	940	50	Opto-29
FPE530	TO-18, Flat Lens	250	1.35	940	5.0	Opto-30

Photosensors

Device No.	Description	I_F mA Max	Diode	Photo-Transistor V_{CE} $I_{CE} = 1.0$ mA V Min	Combined		Package No.
			V_F $I_F = 20$ mA V Typ		I_{OUT} $I_F = 50$ mA, $V_{CE} = 5.0$ V distance = .40" μA Min	μA Max	
FPA103/106	Light Reflective Transducer	75	1.25	12	20	—	Opto-36
FPA104/107	Light Reflective Transducer	75	1.25	12	60	180	Opto-36
FPA105/108	Light Reflective Transducer	75	1.25	12	80	160	Opto-36